OptiMOS®-P2 Power-Transistor

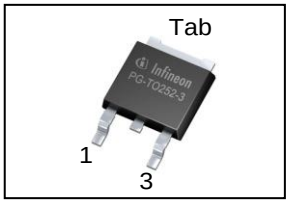
Product Summary

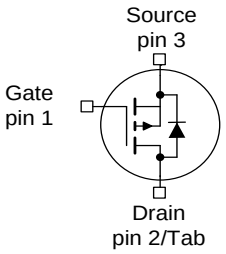
V_{DS}	-40	V
$R_{DS(on)}$	6.4	mΩ
I_D	-85	A

Features

- P-channel - Logic Level - Enhancement mode
- AEC qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green package (RoHS compliant)
- 100% Avalanche tested

PG-TO252-3-313





Type	Package	Marking
IPD85P04P4L-06	PG-TO252-3-313	4P04L06

Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current[1]	I_D	T_C=25°C, V_{GS}=-10V	-85	A
		T_C=100°C, V_{GS}=-10V[2]	-66	
Pulsed drain current[2]	$I_{D,pulse}$	T_C=25°C	-340	
Avalanche energy, single pulse[2]	E_{AS}	I_D=-42.5A	30	mJ
Avalanche current, single pulse	I_{AS}	-	-85	A
Gate source voltage	V_{GS}	-	+5/-16	V
Power dissipation	P_{tot}	T_C=25 °C	88	W
Operating and storage temperature	T_j, T_{stg}	-	-55 ... +175	°C
IEC climatic category; DIN IEC 68-1	-	-	55/175/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics[2]						
Thermal resistance, junction - case	R_{thJC}	-	-	-	1.7	K/W
SMD version, device on PCB	R_{thJA}	minimal footprint	-	-	62	
		6 cm^2 cooling area[3]	-	-	40	
Electrical characteristics, at T_j=25 °C, unless otherwise specified						
Static characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D= -1mA	-40	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=-150µA	-1.2	-1.7	-2.2	
Zero gate voltage drain current	I_{DSS}	V_{DS}=-32V, V_{GS}=0V, T_j=25°C	-	-0.05	-1	µA
		V_{DS}=-32V, V_{GS}=0V, T_j=125°C[2]	-	-20	-200	
Gate-source leakage current	I_{GSS}	V_{GS}=-16V, V_{DS}=0V	-	-	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=-4.5V, I_D=-50A	-	7.7	10.3	mΩ
		V_{GS}=-10V, I_D=-85A	-	5.3	6.4	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics[2]						
Input capacitance	C_{iss}	V_{GS}=0V, V_{DS}=-25V, f=1MHz	-	5060	6580	pF
Output capacitance	C_{oss}		-	1520	2280	
Reverse transfer capacitance	C_{rss}		-	60	120	
Turn-on delay time	$t_{d(on)}$	V_{DD}=-20V, V_{GS}=-10V, I_D=-85A, R_G=3.5Ω	-	17	-	ns
Rise time	t_r		-	10	-	
Turn-off delay time	$t_{d(off)}$		-	62	-	
Fall time	t_f		-	39	-	
Gate Charge Characteristics[2]						
Gate to source charge	Q_{gs}	V_{DD}=-32V, I_D=-85A, V_{GS}=0 to -10V	-	19	25	nC
Gate to drain charge	Q_{gd}		-	13	26	
Gate charge total	Q_g		-	80	104	
Gate plateau voltage	$V_{plateau}$		-	-3.5	-	V
Reverse Diode						
Diode continous forward current[2]	I_S	T_C=25°C	-	-	-85	A
Diode pulse current[2]	$I_{S,pulse}$		-	-	-340	
Diode forward voltage	V_{SD}	V_{GS}=0V, I_F=-85A, T_j=25°C	-	-1	-1.3	V
Reverse recovery time[2]	t_{rr}	V_R=-20V, I_F=-50A, di_F/dt=-100A/µs	-	56	-	ns
Reverse recovery charge[2]	Q_{rr}		-	64	-	nC

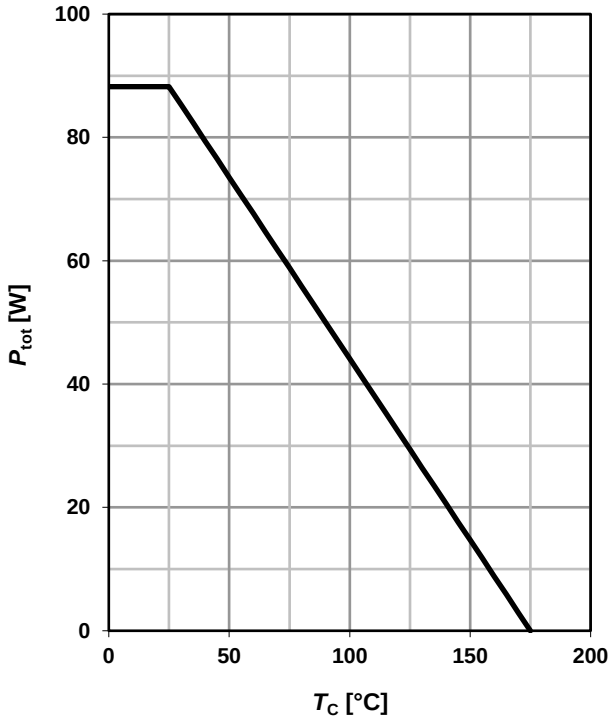
[1] Current is limited by bondwire; with an R_{thJC} = 1.7K/W the chip is able to carry -94A at 25°C.

[2] Defined by design. Not subject to production test.

[3] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm^2 (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

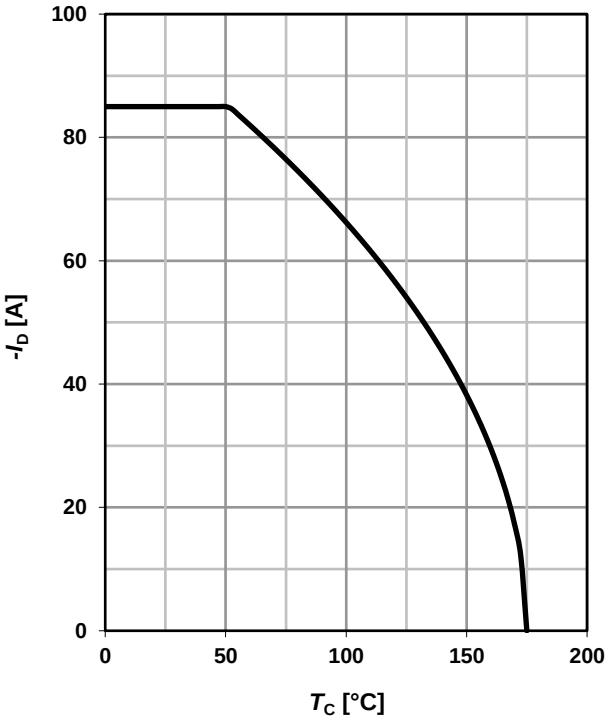
1 Power dissipation

$P_{tot} = f(T_C)$; $V_{GS} \leq -6V$



2 Drain current

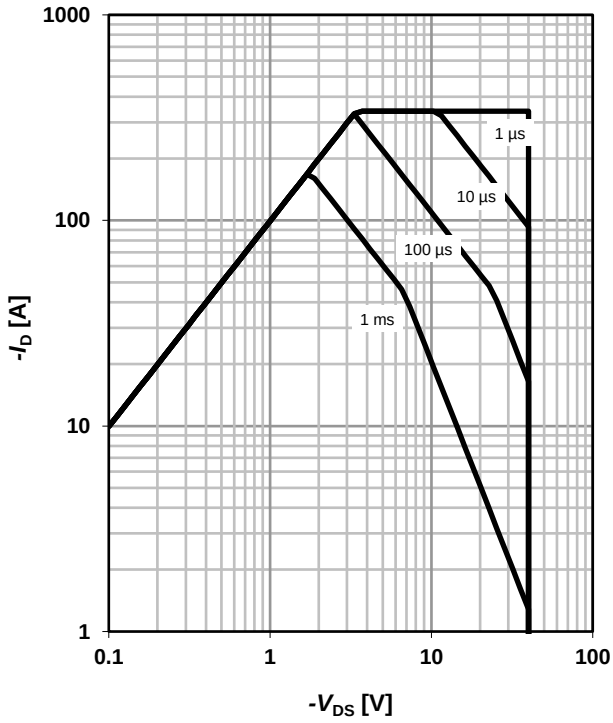
$I_D = f(T_C)$; $V_{GS} = -10V$



3 Safe operating area

$I_D = f(V_{DS})$; $T_C = 25$ °C; $D = 0$

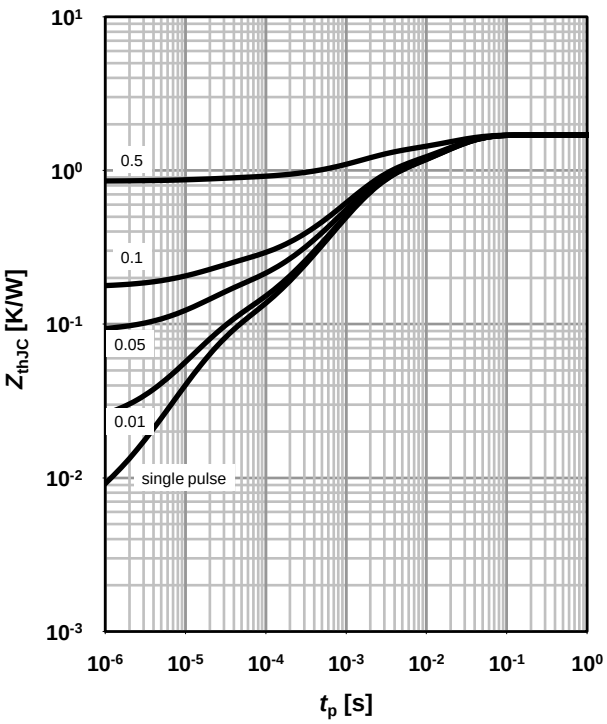
parameter: t_p



4 Max. transient thermal impedance

$Z_{thJC} = f(t_p)$

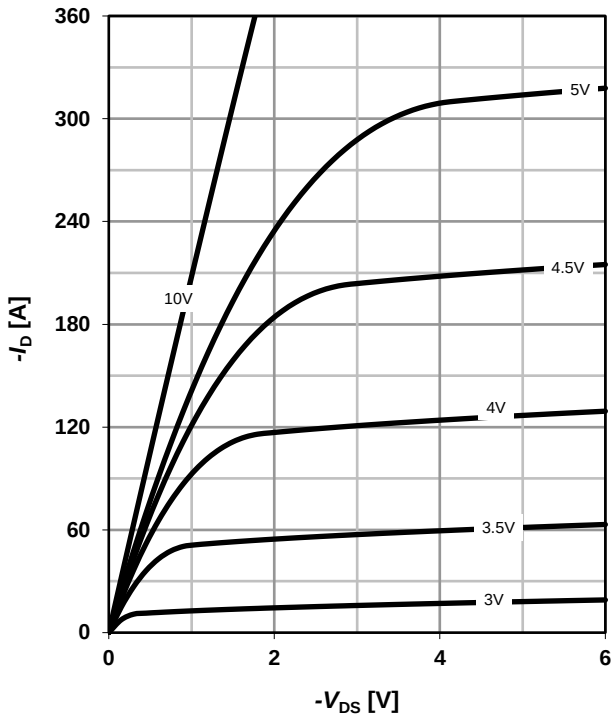
parameter: $D = t_p/T$



5 Typ. output characteristics

$I_D = f(V_{DS})$; $T_j = 25$ °C

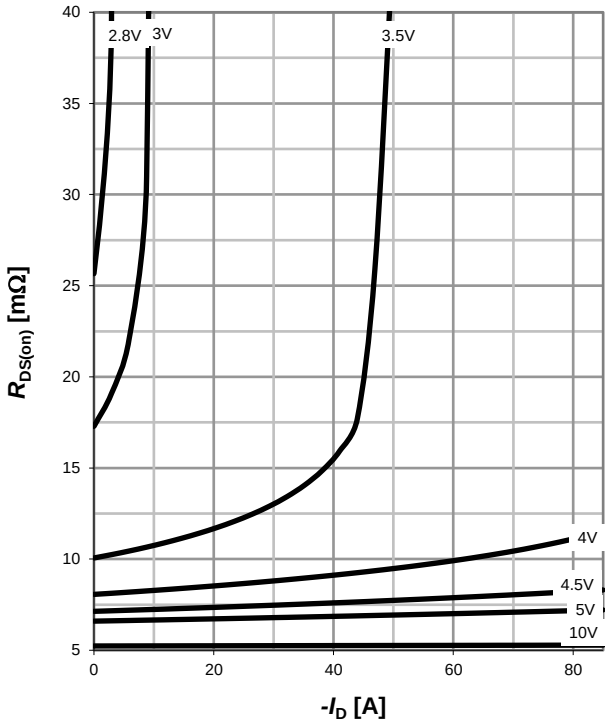
parameter: $-V_{GS}$



6 Typ. drain-source on-state resistance

$R_{DS(on)} = (I_D)$; $T_j = 25$ °C

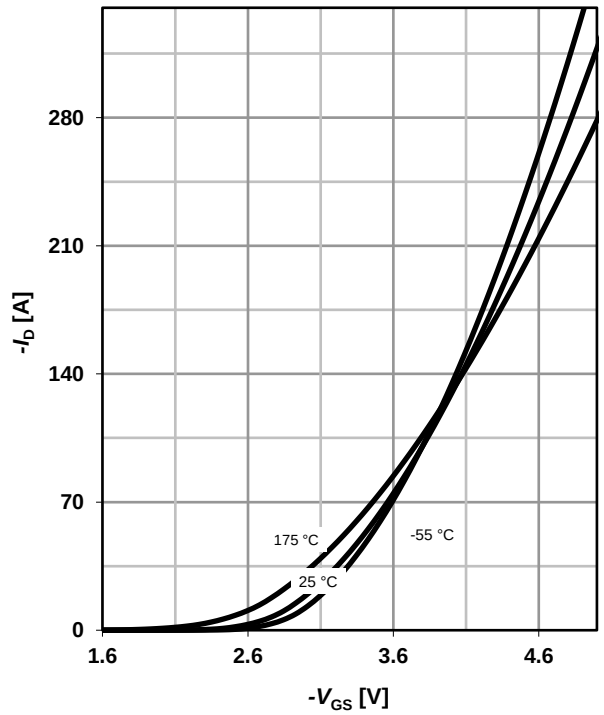
parameter: $-V_{GS}$



7 Typ. transfer characteristics

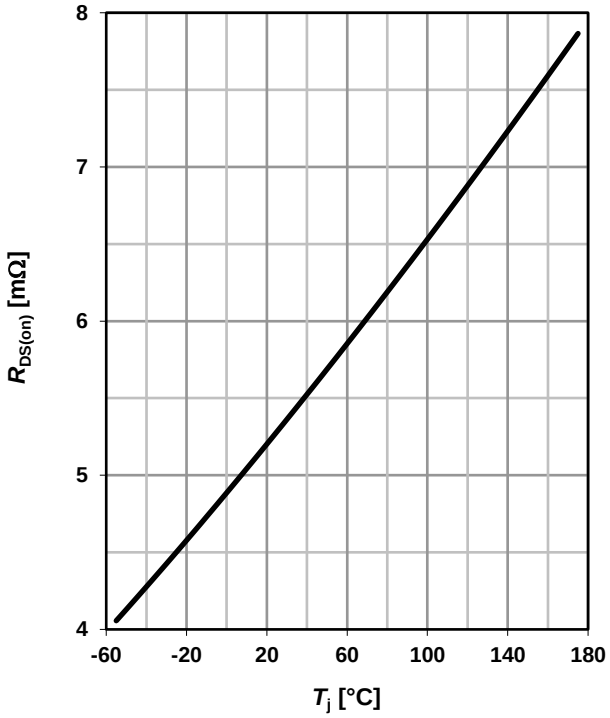
$I_D = f(V_{GS})$; $V_{DS} = -6$V

parameter: T_j



8 Typ. drain-source on-state resistance

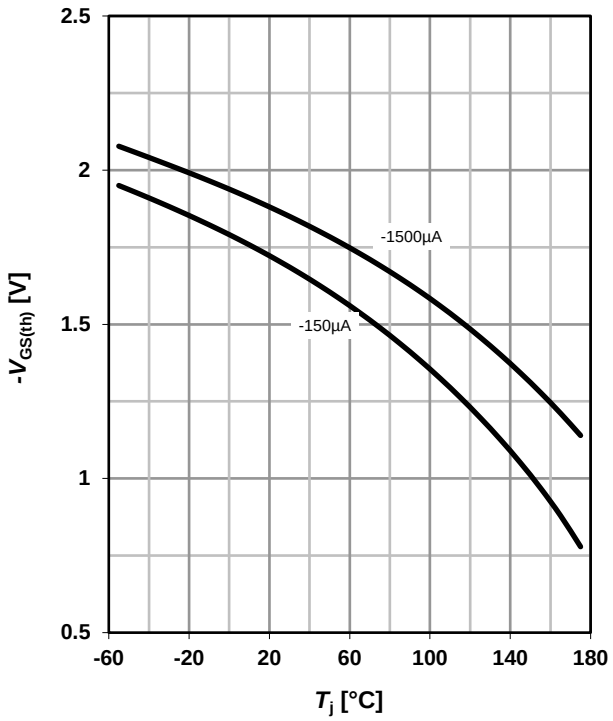
$R_{DS(on)} = f(T_j)$; $I_D = -85$ A; $V_{GS} = -10$ V



9 Typ. gate threshold voltage

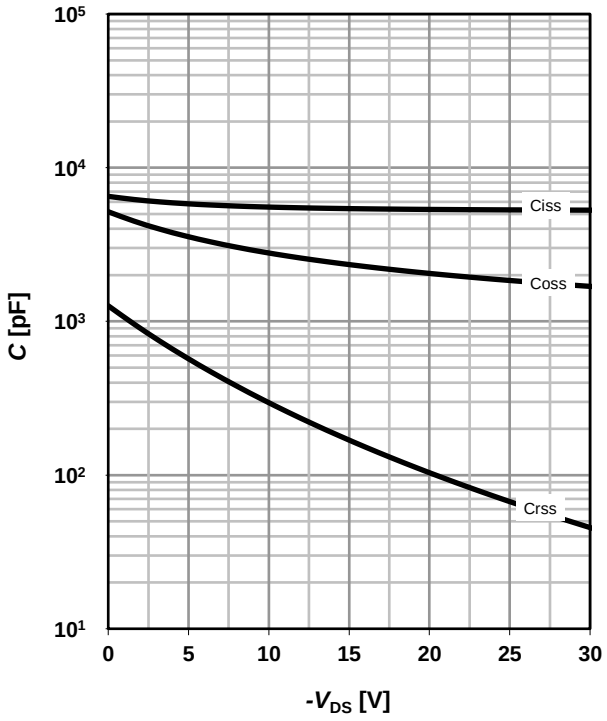
$V_{GS(th)} = f(T_j)$; $V_{GS} = V_{DS}$

parameter: $-I_D$



10 Typ. capacitances

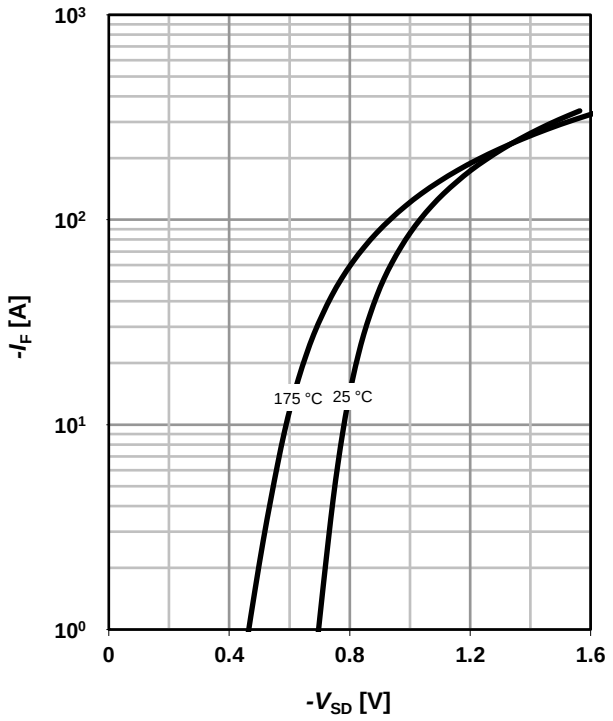
$C = f(V_{DS})$; $V_{GS} = 0$ V; $f = 1$ MHz



11 Typical forward diode characteristicis

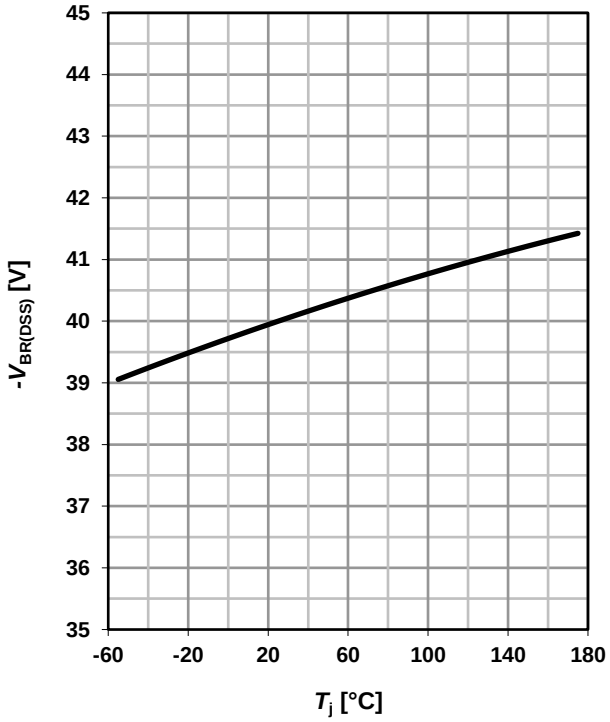
IF = f(V_{SD})

parameter: T_j



12 Drain-source breakdown voltage

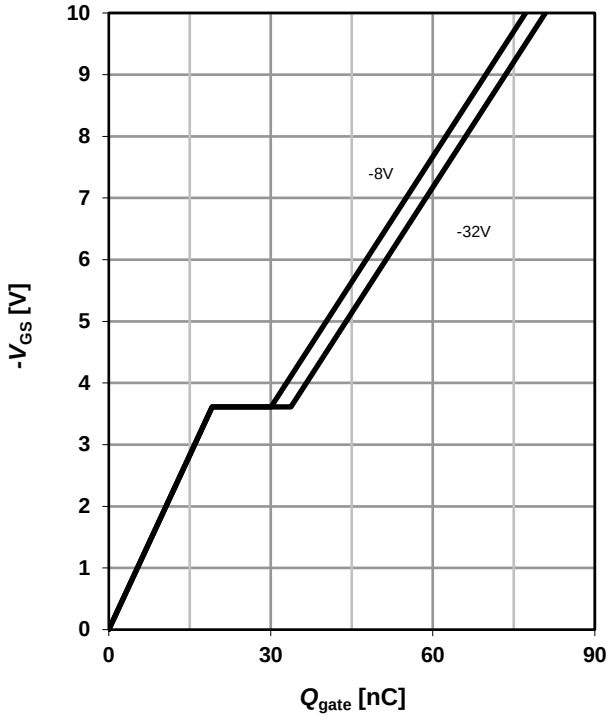
$V_{BR(DSS)} = f(T_j)$; $I_D = -1$ mA



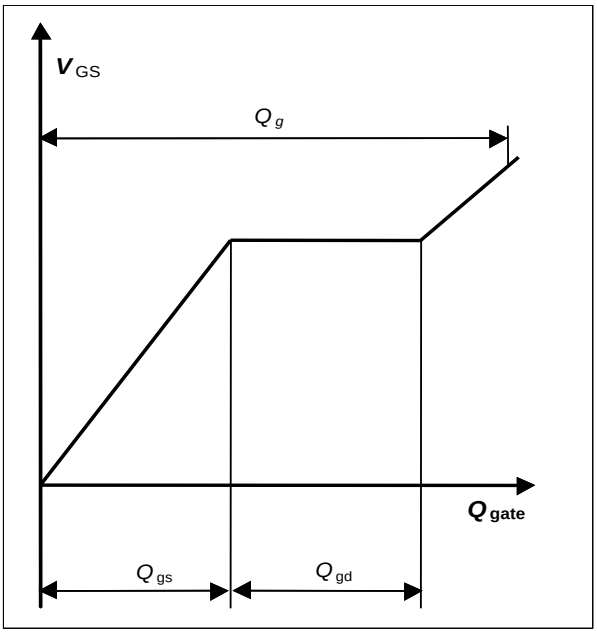
13 Typ. gate charge

V_{GS} = f(Q_{gate}); I_D = -85 A pulsed

parameter: V_{DD}



14 Gate charge waveforms



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Revision History

Version	Date	Changes
1.0	14.03.2011	Final Data Sheet
1.1	04.07.2019	V_{GS} changed